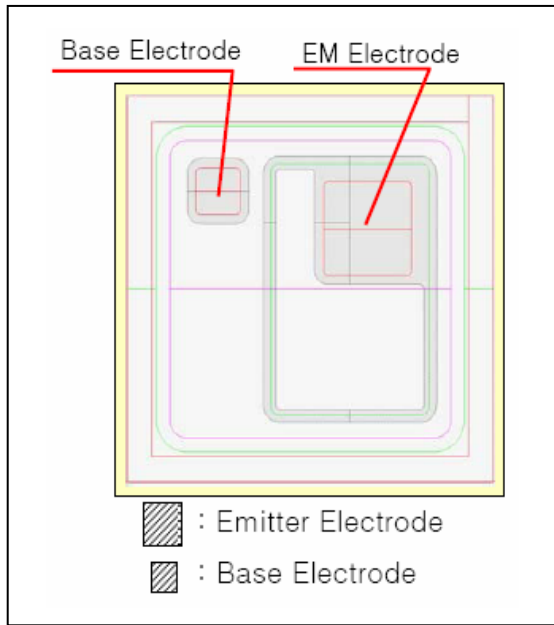


OPB0422

Silicon Photo Transistor

1. Structure

- 1.1 Chip Size : 0.415mm X 0.415mm
- 1.2 Chip thickness : $180 \pm 15 \mu\text{m}$
- 1.3 Metallization : Top - Al, Bottom - Au
- 1.4 Passivation : Silicon Nitride
- 1.5 Bonding Pad Size
 - Emitter : $138 \mu\text{m} \times 138 \mu\text{m}$
 - Base : $70 \mu\text{m} \times 70 \mu\text{m}$



2. Guaranteed Probed Electrical Characteristics

($T_a=25^\circ\text{C}$)

Parameter	Symbol	Min	Typ	Max	Unit	Condition
C-E Leakage Current	I_{CEO}			50	nA	$V_{ce}=20\text{V}$
Spectrum Sensitivity	λ	500		1,050	nm	
Peak Sensing Wavelength	λ_p		880		nm	
C-E Voltage	BV_{CEO}	90			V	$I_{CE}=500\mu\text{A}$
C-B Voltage	BV_{CBO}	100			V	$I_{CB}=50\mu\text{A}$
E-B Voltage	BV_{EBO}	6.7			V	$I_{EB}=50\mu\text{A}$
E-C Voltage	BV_{ECO}	7.1			V	$I_{EC}=50\mu\text{A}$
C-E Saturation Voltage	V_{CES}			200	mV	$I_C=5\text{mA}, I_B=1\text{mA}$
DC Current Gain	h_{FE}	700		1,500	-	$V_{CE}=10\text{V}, I_c=1\text{mA}$

3. Absolute Maximum Ratings

($T_a=25^\circ\text{C}$)

Parameter	Symbol	Rating	Unit
Collector-Emitter Voltage	V_{CEO}	90	V
Emitter-Collector Voltage	V_{ECO}	7.1	V

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